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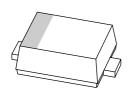
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Kind regards,

Team Nexperia



# 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier Rev. 01 — 11 August 2009

Product data sheet

#### **Product profile** 1.

### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD123W small and flat lead Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features

- Average forward current:  $I_{F(AV)} \le 3 A$
- Reverse voltage: V<sub>R</sub> ≤ 40 V
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

### **1.3 Applications**

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

### 1.4 Quick reference data

#### Table 1. Quick reference data

 $T_i = 25 \circ C$  unless otherwise specified.

)	1					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub> average forward current		square wave; $\delta = 0.5;$ f = 20 kHz				
		$T_{amb} \le 40 \ ^{\circ}C$	<u>[1]</u> _	-	3	А
		$T_{sp} \le 130 \ ^{\circ}C$	-	-	3	А
V <sub>R</sub>	reverse voltage		-	-	40	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 3 A	-	460	540	mV
I <sub>R</sub>	reverse current	V <sub>R</sub> = 40 V	-	25	100	μA

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

# 2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	
2	anode	1 2	1 🕂 2
			sym001

[1] The marking bar indicates the cathode.

# 3. Ordering information

Table 3. Or	dering informat	ion	
Type number	Package		
	Name	Description	Version
PMEG4030EF	R -	plastic surface-mounted package; 2 leads	SOD123W

## 4. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG4030ER	BF

## 5. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

			,		
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C	-	40	V
I <sub>F(AV)</sub>	average forward current	square wave; $\delta = 0.5;$ f = 20 kHz			
		$T_{amb} \le 40 \ ^{\circ}C$	<u>[1]</u> _	3	А
		$T_{sp} \le 130 \ ^{\circ}C$	-	3	А
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms	[2] -	50	А
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[3][4] _	0.57	W
			[3][5]	0.95	W
			[3][1]	1.8	W

#### 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

#### Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

[2]  $T_j = 25 \,^{\circ}C$  prior to surge.

[3] Reflow soldering is the only recommended soldering method.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	<u>[1][2]</u>			
	junction to ambient		<u>[3]</u> _	-	220	K/W
			<u>[4]</u> _	-	130	K/W
			[5] _	-	70	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		<u>[6]</u> _	-	18	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses  $P_R$  are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

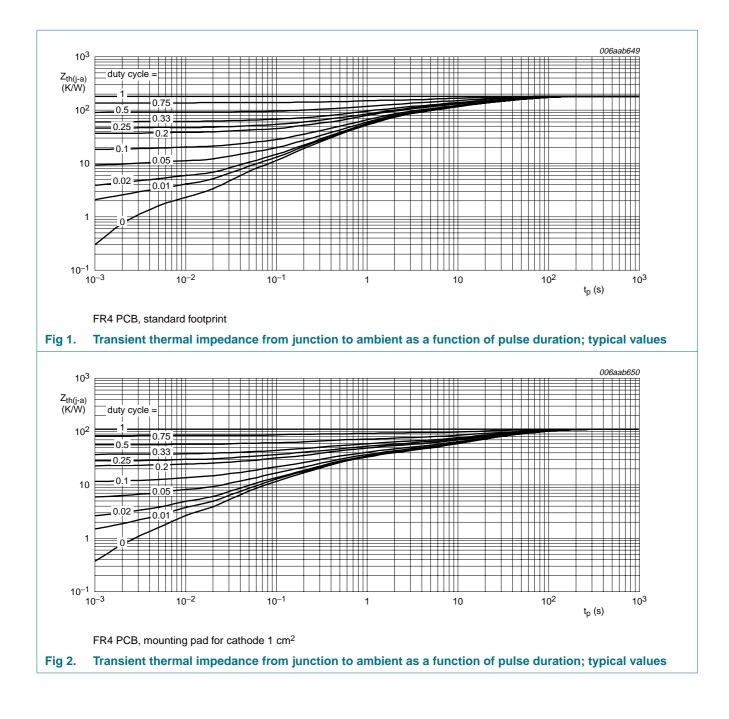
[5] Device mounted on a ceramic PCB,  $AI_2O_3$ , standard footprint.

[6] Soldering point of cathode tab.

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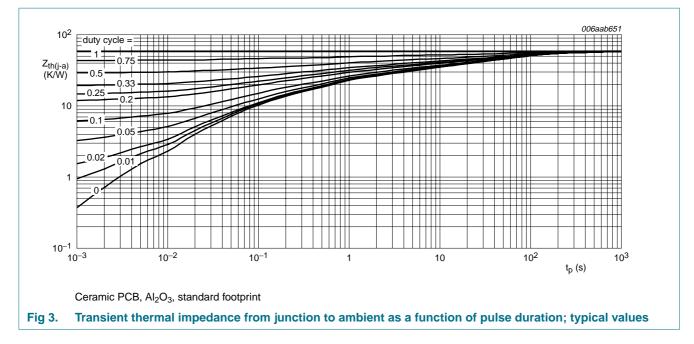
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#### 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

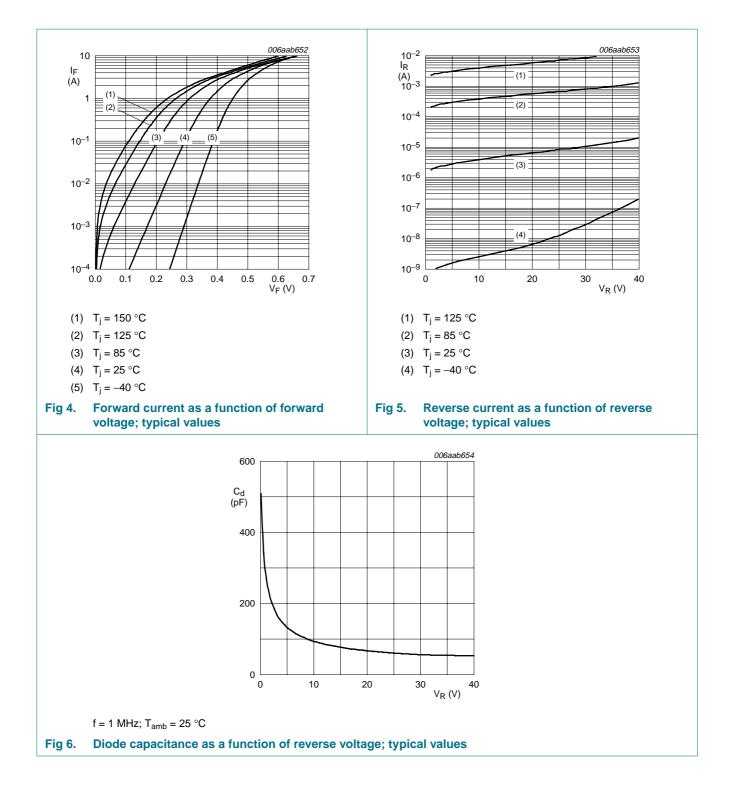


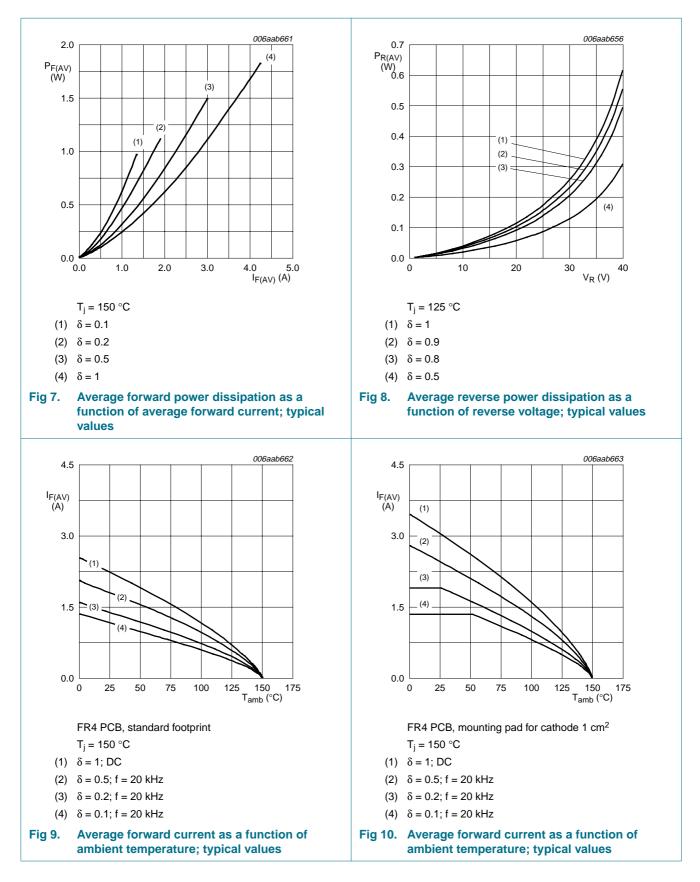
## 7. Characteristics

 Table 7.
 Characteristics

Ti	= 25 °C	unless	otherwise	specified.
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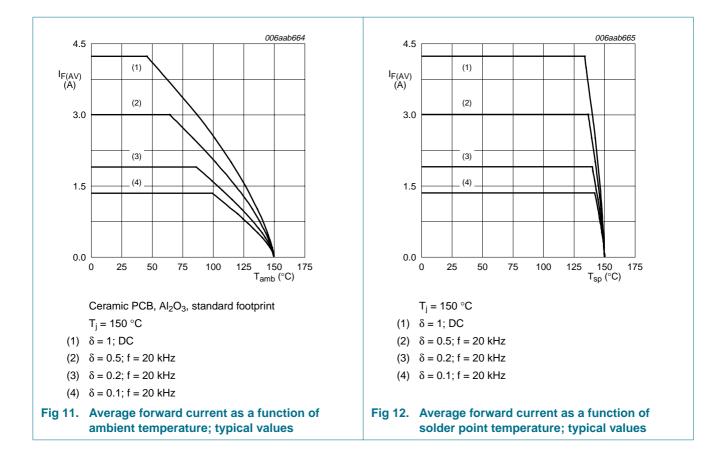
,	'					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 0.1 A	-	295	330	mV
	I <sub>F</sub> = 1 A	-	380	440	mV	
	I <sub>F</sub> = 3 A	-	460	540	mV	
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V	-	5	-	μA
		V <sub>R</sub> = 40 V	-	25	100	μA
C <sub>d</sub>	diode capacitance	f = 1 MHz				
	$V_R = 1 V$	-	250	-	pF	
		V <sub>R</sub> = 10 V	-	95	-	pF





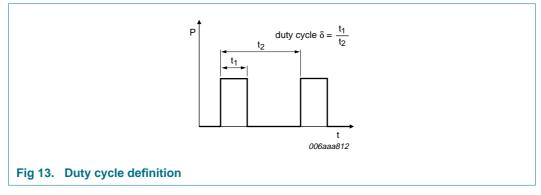
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#### 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

### 8. Test information

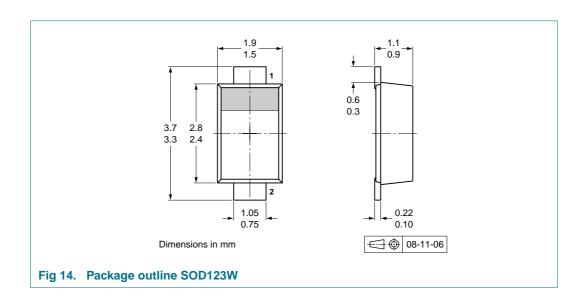


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,

 $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with I<sub>RMS</sub> defined as RMS current.

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.



### 9. Package outline

PMEG4030ER 1

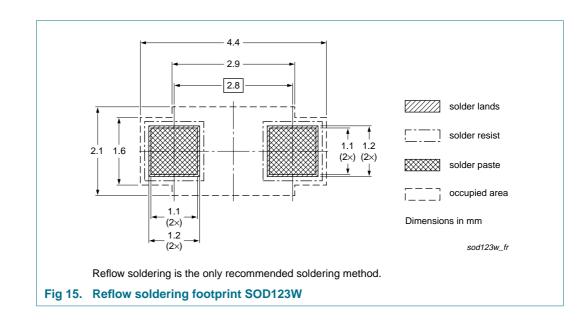
3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

## **10. Packing information**

	king methods xx are the last	three digits of the 12NC ordering code.[1]	
Type numberPackageDescriptionPacking quantity			
			3000
PMEG4030ER	SOD123W	4 mm pitch, 8 mm tape and reel	-115
[1] For further inf	ormation and the	availability of packing methods, see Section	14

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

## 11. Soldering



### 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

# 12. Revision history

Table 9. R	evision histo	ory			
Document ID	)	Release date	Data sheet status	Change notice	Supersedes
PMEG4030E	R_1	20090811	Product data sheet	-	-

#### 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

## **13. Legal information**

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

#### 3 A low V<sub>F</sub> MEGA Schottky barrier rectifier

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